

20V N-Channel MOSFET



TO-252

Pin Definition:

- 1. Gate
- 2. Drain
- 3. Source



V_{DS} (V) $R_{DS(on)}(m\Omega)$ $I_D(A)$ 30 @ V_{GS} = 10V 8 20 6 40 @ V_{GS} = 4.5V

PRODUCT SUMMARY

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

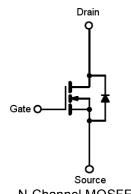
Application

- Load Switch
- PA Switch

Ordering Information

Part No.	Package	Packing	
TSM12N02CP RO	TO-252	T&R	

Block Diagram



N-Channel MOSFET

Absolute Maximum Rating (Ta = 25 °C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V_{DS}	20	V	
Gate-Source Voltage		V_{GS}	±12	V	
Continuous Drain Current, V _{GS} @4.5V.		I _D	12	Α	
Pulsed Drain Current, V _{GS} @4.5V		I _{DM}	30	Α	
Continuous Source Current (Diode Conduction) ^{a,b}		I _S	1.7	Α	
Maximum Power Dissipation	Ta = 25 °C	Ь	60	W	
	Ta = 70 °C	P _D	23		
Operating Junction Temperature		T_J	+150	°C	
Operating Junction and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C	

Thermal Performance

Parameter	Symbol	Limit	Unit
Lead Temperature (1/8" from case)	T_L	10	S
Junction to Case Thermal Resistance	$R\Theta_{JC}$	2.2	°C/W
Junction to Ambient Thermal Resistance (PCB mounted)	R⊖JA	50	°C/W

Notes:

- a. Maximum DC current limited by the package
- b. Surface Mounted on 1" x 1" FR4 Board, t ≤ 10 sec.



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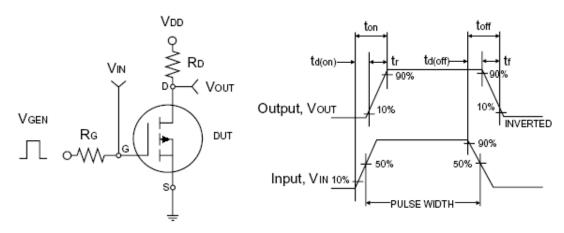


Electrical Specifications

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250uA$	BV _{DSS}	20			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250uA$	$V_{GS(TH)}$	0.6			V
Gate Body Leakage	$V_{GS} = \pm 12V, V_{DS} = 0V$	I _{GSS}			±100	nA
Zero Gate Voltage Drain Current	$V_{DS} = 20V, V_{GS} = 0V$	I _{DSS}			1.0	uA
On-State Drain Current	V _{DS} ≥5V, V _{GS} = 10V	I _{D(ON)}	12			Α
Drain-Source On-State Resistance	$V_{GS} = 4.5V, I_D = 6A$			30	40	m0
	Drain-Source On-State Resistance $V_{GS} = 10V, I_D = 8A$ $R_{DS(ON)}$		21	30	mΩ	
Forward Transconductance	$V_{DS} = 10V, I_{D} = 6A$	g _{fs}	7	13		S
Diode Forward Voltage	$I_S = 1.7A, V_{GS} = 0V$	V_{SD}	1	-	1.2	V
Dynamic ^b						
Total Gate Charge	$V_{DS} = 10V, I_D = 6A,$	Q_g		4.86		
Gate-Source Charge		Q_{gs}		0.92		nC
Gate-Drain Charge	$V_{GS} = 4.5V$	Q_{gd}		1.4		
Input Capacitance	.,	C _{iss}		562		
Output Capacitance	$V_{DS} = 8V, V_{GS} = 0V,$ f = 1.0MHz	C _{oss}		106		pF
Reverse Transfer Capacitance	1 - 1.0101112	C _{rss}	1	75		
Switching ^c						
Turn-On Delay Time	1011	$t_{d(on)}$		8.1		
Turn-On Rise Time	$V_{DD} = 10V, I_D = 1A,$	t _r	1	9.95		nS
Turn-Off Delay Time	$V_{GEN} = 10V$, $R_G = 16\Omega$	t _{d(off)}		21.85		113
Turn-Off Fall Time	1032	t _f		5.35		

Notes:

- a. pulse test: PW ≤300µS, duty cycle ≤2%
- b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



Switching Test Circuit

Switchin Waveforms



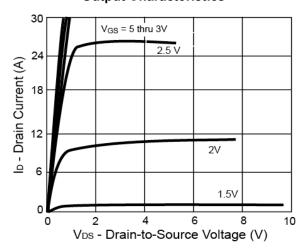


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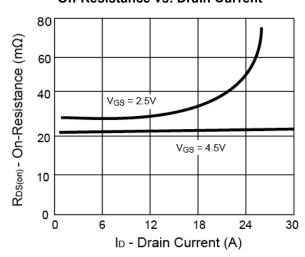


Electrical Characteristics Curve (Ta = 25 °C, unless otherwise noted)

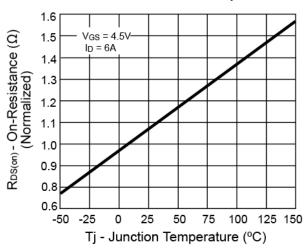
Output Characteristics



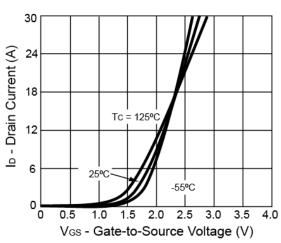
On-Resistance vs. Drain Current



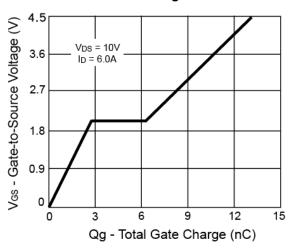
On-Resistance vs. Junction Temperature



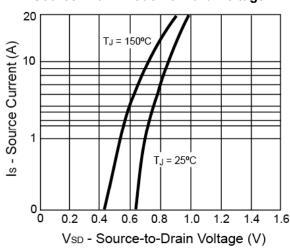
Transfer Characteristics



Gate Charge



Source-Drain Diode Forward Voltage





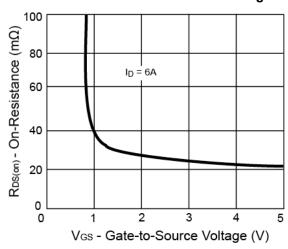




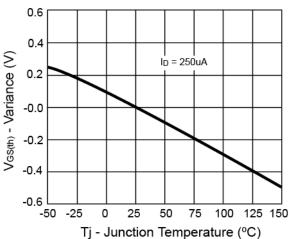


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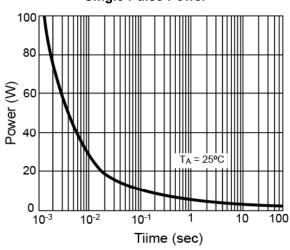
On-Resistance vs. Gate-Source Voltage



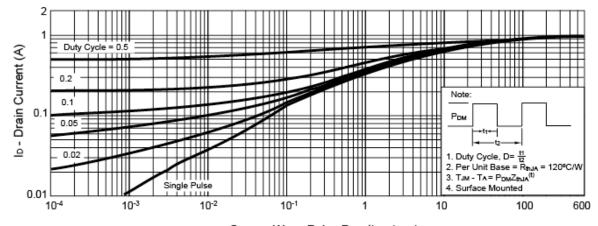
Threshold Voltage



Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient



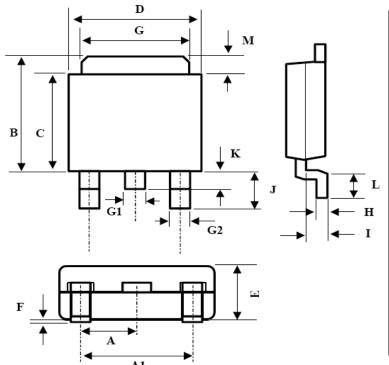
Square Wave Pulse Duration (sec)



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SOT-252 Mechanical Drawing



TO-252 DIMENSION						
		MILLIMETERS		INCHES		
DIM	MIN	MAX	MIN	MAX		
Α	2.3E	BSC	0.09BSC			
A1	4.6BSC		0.18BSC			
В	6.80	7.20	0.268	0.283		
С	5.40	5.60	0.213	0.220		
D	6.40	6.65	0.252	0.262		
Е	2.20	2.40	0.087	0.094		
F	0.00	0.20	0.000	0.008		
G	5.20	5.40	0.205	0.213		
G1	0.75	0.85	0.030	0.033		
G2	0.55	0.65	0.022	0.026		
Н	0.35	0.65	0.014	0.026		
I	0.90	1.50	0.035	0.059		
J	2.20	2.80	0.087	0.110		
K	0.50	1.10	0.020	0.043		
L	0.90	1.50	0.035	0.059		
М	1.30	1.70	0.051	0.67		



TSM12N02 20V N-Channel MOSFET

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